

Ultra-Low power CMOS Output Hall Switch

MH235 Hall-effect sensor is a temperature stable, stress-resistant, Low Tolerance of Sensitivity Ultra-power switch. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

MH235 is special made for low operation voltage, 2.7V, to active the chip which is includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, CMOS output driver. Advanced CMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries. This device requires the presence of omni-polar magnetic fields for operation.

The package type is in a Halogen Free version has been verified by third party Lab.

Features and Benefits

- Output-on & Inverted Output-on without Magnet present in one chip
- Low and high Hz presented in one chip
- Strong RF noise protection
- 2.7 to 5.5V for battery-powered applications
- Omni polar, output switches with absolute value of North or South pole from magnet
- Operation down to 2.7V
- High Sensitivity for reed switch replacement applications
- Multi Small Size option
- Low sensitivity drift in crossing of Temp. range
- Ultra-Low power consumption at 1.6uA (Avg)
- High ESD Protection, HBM>±4KV(min)
- Totem-pole output
- RoHS compliant 2011/65/EU and Halogen Free.

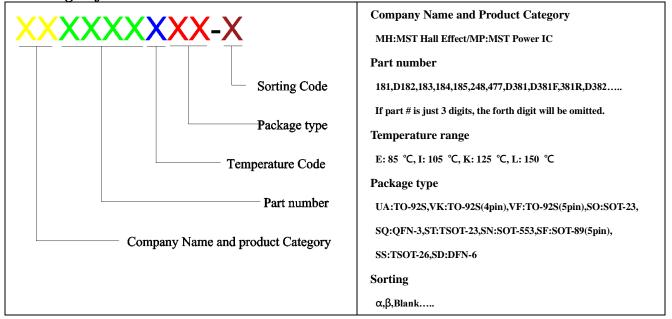
Applications

- Solid state switch
- Handheld Wireless Handset Awake Switch
- Lid close sensor for battery powered devices
- Magnet proximity sensor for reed switch replacement in low duty cycle applications
- Floating Meter
- Security
- 3C
- Smart Meter
- TWS



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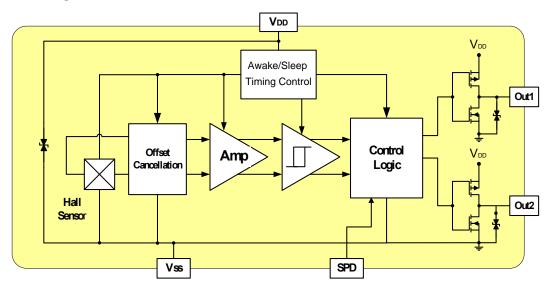
Ordering Information



Part No.	Temperature Suffix	Package Type
MH235EST	$E \left(-40^{\circ}C \text{ to } + 85^{\circ}C\right)$	ST(TSOT-23)
MH235EUA	$E \left(-40^{\circ}C \text{ to } + 85^{\circ}C\right)$	UA(TO-92S)
MH235ESD	E $(-40^{\circ}\text{C to } +85^{\circ}\text{C})$	SD (DFN2X2-6L)
MH235ESS	E $(-40^{\circ}\text{C to} + 85^{\circ}\text{C})$	SS (QFN1x1-4L)

Custom sensitivity selection is available by MST sorting technology

Functional Diagram



Note: Static sensitive device; please observe ESD precautions. Reverse V_{DD} protection is not included. For reverse voltage protection, a 100Ω resistor in series with V_{DD} is recommended.

MH 235, HBM>±4KV which is verified by third party lab.



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Absolute Maximum Ratings At(Ta=25°C)

Characteristics		Values	Unit
Supply voltage,(VDD)		6	V
Output Voltage,(Vout)		6	V
Magnetic flux density		Unlimited	Gauss
Output current,(Iovr)		5	mA
Operating temperature range, (Ta)		-40 to +85	°C
Storage temperature range, (Ts)		-65 to +150	°C
Maximum Junction Temp,(Tj)		150	°C
Thermal Resistance	(θ _{JA}) UA/ST/SS/SD	206/543/300/160	°C/A
	(θ _{JC}) UA/ST/SS/SD	148/410/52/35	°C/A
Package Power Dissipation, (P _D) UA/ST/SS/SD		606/400/416/780	mW

Note: Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

Electrical Specifications

DC Operating Parameters: Ta=25°C, VDD=3.0V

Parameters	Test Conditions	Min	Тур	Max	Units
Supply Voltage, (V_{DD})	Operating	2.7		5.5	Volts
	Awake State		2.0		mA
Supply Current, (<i>I</i> _{DD})	Sleep State		1.0		μΑ
	Average (SPD=Hi)		1.6(135)		μΑ
Output High Voltage, (VoH)	IOUT=1.0mA (Source)	V _{DD} -0.2			V
Output Low Voltage, (Vol)	Iout=1.0mA (Sink)			0.2	V
Awake mode time, (<i>Taw</i>)	Operating		20	40	uS
Sleep mode time, (<i>Tsl.</i>)	Operating (SPD=Hi)		80(0.16)	150(0.32)	mS
Duty Cycle, (<i>D</i> , <i>C</i>)	(SPD=Hi)		0.025(12.5)		%
Power-On Time, (T_{PO})			16	32	nS
Output Switch Time, (T_{SW})	Operating (SPD=Hi)		80(0.2)	160(0.4)	mS
Output Switch Frequency, (F_{SW})	Operating (SPD=Hi)	15(6.5k)			Hz
Electro-Static Discharge	HBM	4			KV
Operate Point, BOPS(BOPN)	B>B _{OP} X	20(-55)		55(-20)	Gauss
Release Point, BRPS(BRPN)	B <b<sub>RPX</b<sub>	10(-45)		45(-10)	Gauss
Hysteresis, (BHYS)	BOPX - BRPX		10		Gauss

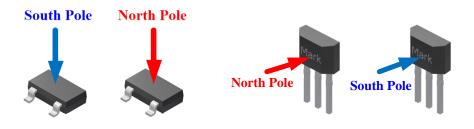


Ultra-Low power CMOS Output Hall Switch

MH235 ST/UA Output Behavior versus Magnetic Polar

DC Operating Parameters: $Ta = -40 \text{ to } 85^{\circ}\text{C}$, Vdd = 2.7V to 5.5V

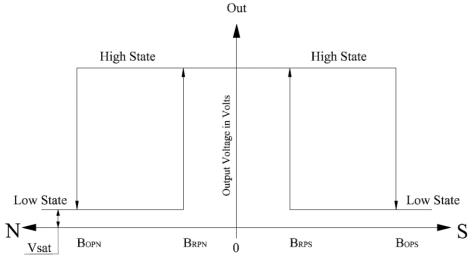
Parameter	Test condition	OUT
South pole	B>Bop-S	Low
Null or weak magnetic field	$B=0 \text{ or } B < \mid B_{RP}X \mid$	High
North pole	B> Bop-N	Low



ST Package

UA Package

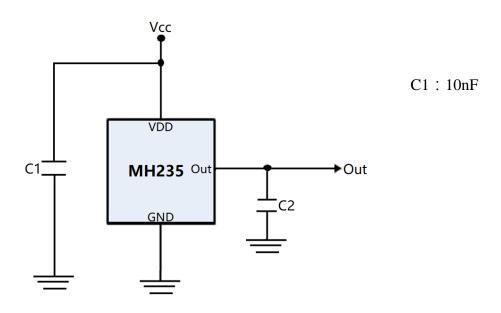
Output Behavior



Magnetic Flux Density in Gauss

Ultra-Low power CMOS Output Hall Switch

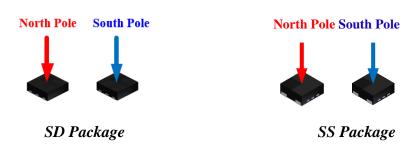
ST and UA package Typical Application Circuit



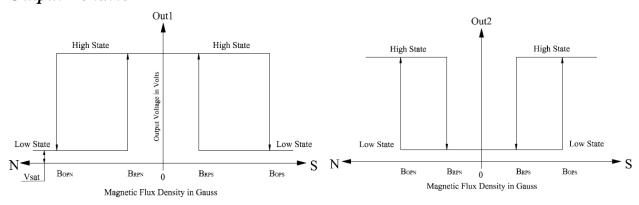
MH235 SS/SD Output Behavior versus Magnetic Polar

DC Operating Parameters: $Ta = -40 \text{ to } 85^{\circ}\text{C}$, Vdd = 2.7V to 5.5V

Parameter	Test condition	OUT1	OUT2
South pole	B>Bop-S	Low	High
Null or weak magnetic field	$B=0 \text{ or } B < \mid B_{RP}-X \mid$	High	Low
North pole	B> Bop-N	Low	High

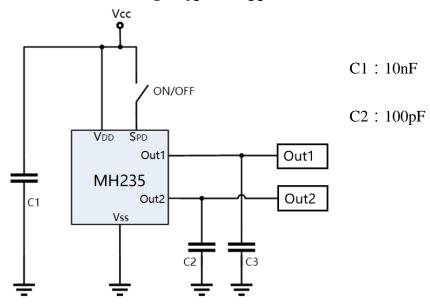


Output Behavior



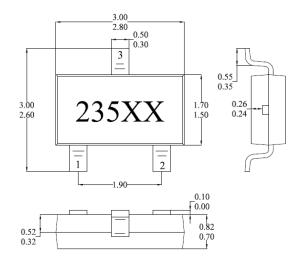
Ultra-Low power CMOS Output Hall Switch

SS and SD Package Typical Application circuit



Sensor Location, package dimension and marking ST Package (TSOT-23)

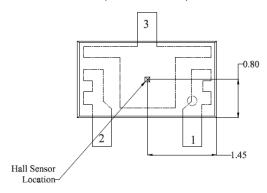
(Top View)



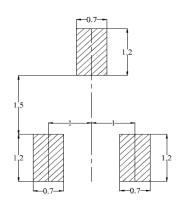
NOTES:

- PINOUT (See Top View at left :)
 Pin 1 V_{DD}; Pin 2 Output; Pin 3 GND
- 2. Controlling dimension: mm
- 3. Lead thickness after solder plating will be 0.254mm maximum
- 4. XX: Date Code, Refer to DC table

Hall Plate Chip Location (Bottom view)



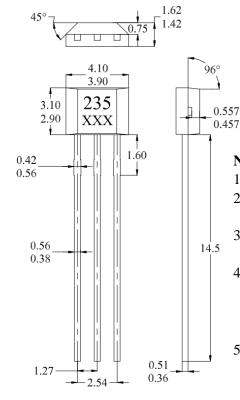
(For reference only) Land Pattern



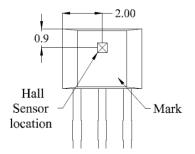


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UA Package (TO-92)

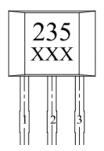


Hall Chip location



Output Pin Assignment

(Top view)



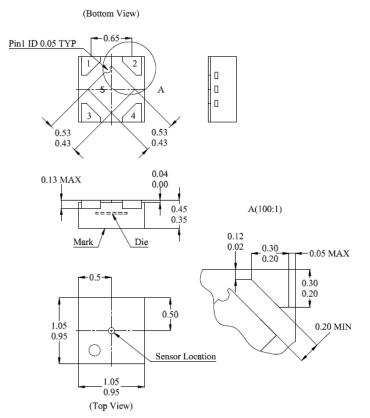
NOTES:

- 1. Controlling dimension: mm
- 2. Leads must be free of flash and plating voids
- 3. Do not bend leads within 1 mm of lead to package interface.
- 4. PINOUT:

Pin 1 VCC Pin 2 GND Pin 3 Output

5. XXX; 1st X=Year; 2nd and 3rd XX=Week

SS Package (DFN 1.0*1.0-4L)



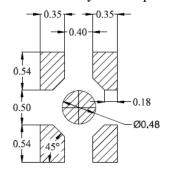
NOTES:

- 1. Controlling dimension: mm
- 2. Leads must be free of flash and plating voids
- 3. Lead thickness after solder plating will be 0.254mm maximum

4. PINOUT:

Pin No.	Pin Name	Function
1	$V_{ m DD}$	Power Supply
2	Vss	Ground
3	Vout	Output1
4	Vout	Output2
5	PAD	Ground

4. (For reference only) Land pattern

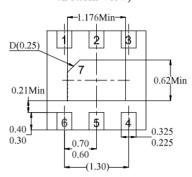


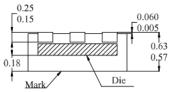


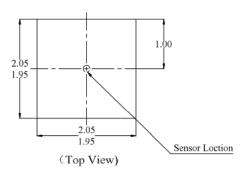
Ultra-power, Totem Pole Output Hall Effect Switch

SD package (DFN2*2-6L)

(Bottom View)







NOTES:

- 1. Controlling dimension: mm
- 2. Leads must be free of flash and plating voids
- 3. Lead thickness after solder plating will be 0.254mm maximum

4. PINOUT:

Pin No.	Pin Name	Function
1	V_{DD}	Power Supply
2	Vout	Output2
3	Vout	Output1
4	N.C	N.C
5	Vss	Ground
6	SPD	Set pin
7	PAD	Ground

5. (For reference only) Land pattern

